

FEATURES

- Frequency band: 57 GHz to 64 GHz**
- Radio frequency (RF) signal modulation bandwidth: up to 1.8 GHz**
- Noise figure (NF): 8 dB typical**
- Receiver gain: 0 dB to 69 dB**
- Digital and analog RF and intermediate frequency (IF) gain control**
- Programmable baseband gain and filter bandwidth**
- Integrated frequency synthesizer**
- Integrated image reject filter**
- Partially external loop filter**
- Support for external local oscillator (LO)**
- On-chip temperature sensor**
- Support for 256 quadrature amplitude modulation (QAM)**
- Integrated AM and FM detectors**
- Universal analog I/Q baseband interface**
- 3-wire serial digital interface**
- 75-ball, RoHS compliant, wafer level ball grid array**

APPLICATIONS

- Small cell backhaul**
- 60 GHz industrial, scientific, and medical (ISM) band data transfer**
- Multiple Gbps data communication**
- WiGig/802.11ad radio**
- High definition video transmission**
- Radar/high resolution imaging**

GENERAL DESCRIPTION

The **HMC6301** is a complete millimeterwave receiver integrated circuit in a 6 mm × 4 mm, RoHS compliant, wafer level ball grid array (WLBGA) that includes a low noise amplifier (LNA), an image reject filter, an RF to IF downconverter, an IF filter, an I/Q downconverter, and a frequency synthesizer. The receiver operates from 57 GHz to 64 GHz with up to 1.8 GHz of double-sided modulation bandwidth.

An integrated synthesizer provides tuning in 250 MHz, 500 MHz, or 540 MHz steps with excellent phase noise to support up to 64 QAM modulation. Optionally, an external LO can be injected allowing for user selectable LO characteristics or phase coherent transmit and receive operation, as well as modulation up to 256 QAM. Support for a wide variety of modulation formats is provided through a universal analog baseband I/Q interface.

The receiver device also contains AM and FM detectors to demodulate on-off keying (OOK), frequency-shift keying (FSK), or minimum-shift keying (MSK) modulation formats for lower cost and lower power serial data links without the need for high speed data converters.

Gain control is provided in the RF, IF, and baseband stages and a low 8 dB typical noise figure is supported at maximum gain. Together with the **HMC6300** transmitter, a complete 60 GHz transmit/receive chipset is provided for multiple Gbps operation in the unlicensed 60 GHz ISM band.

FUNCTIONAL BLOCK DIAGRAM

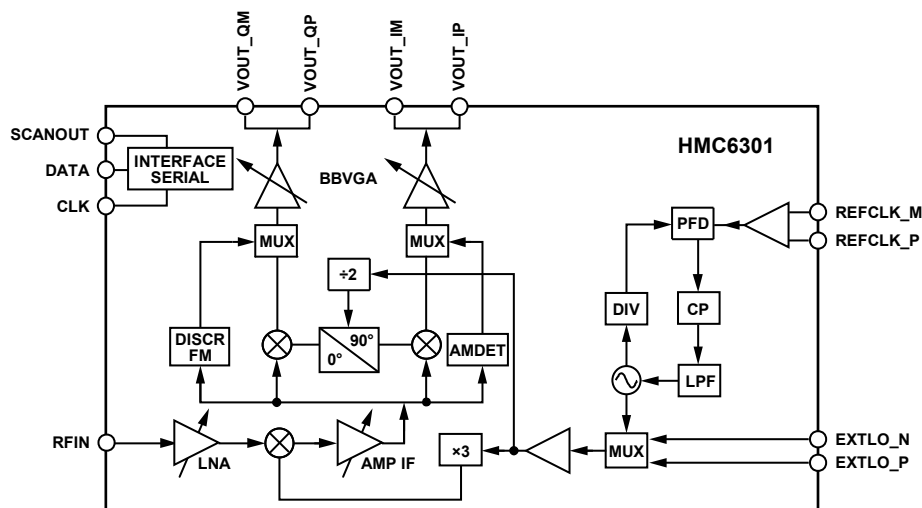


Figure 1.

Rev. A

[Document Feedback](#)

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.
 Tel: 781.329.4700 ©2016 Analog Devices, Inc. All rights reserved.
[Technical Support](#) www.analog.com

TABLE OF CONTENTS

| | | | |
|--|---|--|----|
| Features | 1 | ESD Caution..... | 6 |
| Applications..... | 1 | Pin Configuration and Function Descriptions..... | 7 |
| General Description | 1 | Typical Performance Characteristics | 9 |
| Functional Block Diagram | 1 | Theory of Operation | 12 |
| Revision History | 2 | Register Array Assignment and Serial Interface | 12 |
| Specifications..... | 3 | Receiver Register Array Assignments..... | 13 |
| Electrical Specifications..... | 3 | Applications Information | 21 |
| Recommended Operating Conditions | 4 | Outline Dimensions | 24 |
| Power Consumption | 5 | Ordering Guide | 24 |
| Absolute Maximum Ratings..... | 6 | | |

REVISION HISTORY

9/2016—v00.0716 to Rev. A

| | |
|---|-----------|
| Updated Format..... | Universal |
| Changes to Features Section..... | 1 |
| Changes to Table 1..... | 3 |
| Changes to Parameter and Symbols Columns, Table 3 | 5 |
| Changes to Figure 17..... | 17 |
| Added Ordering Guide | 24 |

7/2016—Revision v00.0716: Initial Version

SPECIFICATIONS

$T_A = 25^\circ\text{C}$, reference frequency = 71.4286 MHz, gain settings = maximum, IF bandwidth = maximum, input impedance = 50 Ω single ended, output impedance = 100 Ω differential, unless otherwise noted.

ELECTRICAL SPECIFICATIONS

Table 1.

| Parameter | Test Conditions/Comments | Min | Typ | Max | Unit |
|--|-----------------------------------|-----|-------|------|------------------|
| FREQUENCY RANGE | | 57 | | 64 | GHz |
| FREQUENCY STEP SIZE | With 71.4286 MHz reference clock | | 250 | | MHz |
| | With 142.857 MHz reference clock | | 500 | | MHz |
| | With 154.2857 MHz reference clock | | 540 | | MHz |
| MODULATION BANDWIDTH | Maximum bandwidth setting | | | | |
| | 3 dB bandwidth | | 1.4 | | GHz |
| | 5 dB bandwidth | | 1.8 | | GHz |
| GAIN | | | | | |
| Maximum Receiver Gain | | 63 | 69 | | dB |
| Minimum Receiver Gain | | | 0 | | dB |
| Baseband Gain Control | High and low gain settings | | 41 | | dB |
| IF Gain Control (Analog/Digital) | | | 12/15 | | dB |
| LNA Gain Control (Analog/Digital) | | | 20/20 | | dB |
| NOISE FIGURE | At maximum gain | | 8 | 13.5 | dB |
| INPUT | Minimum LNA gain | | | | |
| For 1 dB Compression (P1dB) | | | -19 | | dBm |
| Third-Order Intercept (IP3) | | | -9 | | dBm |
| TEMPERATURE SENSOR RANGE | Four levels | -40 | | +85 | $^\circ\text{C}$ |
| SUPPRESSION AND REJECTION | | | | | |
| Image Rejection ($3 \times \text{LO} - \text{IF}$) | | | >35 | | dBc |
| Sideband Suppression (I/Q Balance) | | 20 | 23 | | dBc |
| PHASE | | | | | |
| Phase Noise | | | | | |
| @ 100 kHz Offset | | | -75 | | dBc/Hz |
| @ 1 MHz Offset | | | -93 | | dBc/Hz |
| @ 10 MHz Offset | | | -114 | | dBc/Hz |
| @ 100 MHz Offset | | | -122 | | dBc/Hz |
| Phase-Locked Loop (PLL) Bandwidth | Using internal filter | | 300 | | kHz |
| POWER DISSIPATION | | | | | |
| Single-Ended | | | 0.82 | | W |
| External LO | | | 0.57 | | W |

RECOMMENDED OPERATING CONDITIONS

Table 2.

| Parameter | Symbol | Min | Typ | Max | Unit |
|--|--------------------------|-------|----------------|-------|-------------|
| POWER SUPPLY | | | | | |
| Buffer | VCC _{BUF} | 2.565 | 2.7 | 2.835 | V dc |
| Low Noise Amplifier (LNA) | VDD _{LNA} | 2.565 | 2.7 | 2.835 | V dc |
| Tripler | VCC _{TRIP} | 2.565 | 2.7 | 2.835 | V dc |
| Divider | VCC _{DIV} | 2.565 | 2.7 | 2.835 | V dc |
| Voltage Controlled Oscillator (VCO) | VCC _{VCO} | 2.565 | 2.7 | 2.835 | V dc |
| Intermediate Frequency | VCC _{IF} | 2.565 | 2.7 | 2.835 | V dc |
| Mixer | VCC _{MIX} | 2.565 | 2.7 | 2.835 | V dc |
| Synthesizer | VCC _{SYN} | 1.3 | 1.35 | 1.48 | V dc |
| Digital Circuit | VDD _D | 1.3 | 1.35 | 1.48 | V dc |
| INPUT VOLTAGE RANGE | | | | | |
| Serial Digital Interface | DATA, ENABLE, CLK, RESET | | | | |
| Logic High | | 0.9 | 1.2 | 1.4 | V |
| Logic Low | | -0.05 | +0.1 | +0.3 | V |
| REFERENCE CLOCK | | | | | |
| Reference Clock, Positive LVPECL/LVDS CMOS | REF _{CLKP} | | 3.3/2.5 1.2 | | V V V |
| Reference Clock, Negative LVPECL/LVDS CMOS | REF _{CLKN} | | 3.3/2.5 1.2 | | V V |
| BASEBAND I/Q | | | | | |
| In-Phase Baseband Input Negative (Minus) | VOUT _{IM} | 10 | 50 | 200 | mV p-p |
| Positive | VOUT _{IP} | 10 | 50 | 200 | mV p-p |
| Quadrature Baseband Input Negative (Minus) | VOUT _{QM} | 10 | 50 | 200 | mV p-p |
| Positive | VOUT _{QP} | 10 | 50 | 200 | mV p-p |
| BASEBAND I/Q, COMMON MODE | | | | | |
| In-Phase Baseband Input Negative (Minus) | VOUT _{IM} | | 1.3 | | V |
| Positive | VOUT _{IP} | | 1.3 | | V |
| Quadrature Baseband Input Negative (Minus) | VOUT _{QM} | | 1.3 | | V |
| Positive | VOUT _{QP} | | 1.3 | | V |
| ANALOG GAIN CONTROL | | | | | |
| Low Noise Amplifier | ANACTRL _{LNA} | 0.1 | | 2.0 | V |
| IF Variable Gain Amplifier | ACTL _{IFVGA} | 0.1 | | 2.25 | V |
| EXTERNAL LO | | | | | |
| Positive | EXTLO _P | 0 | 3 | 6 | dBm |
| Negative | EXTLO _N | 0 | 3 | 6 | dBm |
| DRAIN CURRENT | | | | | |
| 1.35 V | | | <1 | | mA |
| 2.7 V | | | 300 | | mA |

POWER CONSUMPTION

Table 3.

| Parameter | Voltage (V) | Typical Current (mA) | Typical Power Consumption (mW) |
|--------------------|-------------|----------------------|--------------------------------|
| VCC _{BUF} | 2.7 | 70 | 189 |
| VCC _{LNA} | 2.7 | 15 | 41 |
| VCC _{TRP} | 2.7 | 54 | 146 |
| VCC _{DIV} | 2.7 | 46 | 124 |
| VCC _{VCO} | 2.7 | 52 | 140 |
| VCC _{IF} | 2.7 | 30 | 81 |
| VCC _{MIX} | 2.7 | 32 | 86 |
| VCC _{SYN} | 1.35 | 0.08 | 0.1 |
| VCC _D | 1.35 | 10 | 13 |

ABSOLUTE MAXIMUM RATINGS

Table 4.

| Parameter | Rating |
|--|------------------|
| VCC _{BUF} | 2.85 V |
| VCC _{LNA} | 2.85 V |
| VCC _{TRIP} | 2.85 V |
| VCC _{DIV} | 2.85 V |
| VCC _{VCO} | 2.85 V |
| VCC _{IF} | 2.85 V |
| VCC _{MIX} | 2.85 V |
| VCC _{SYN} | 1.6 V |
| VDD _D | 1.6 V |
| Serial Digital Interface Input Voltage | 1.5 V |
| Baseband Outputs: BB, FM (Each) | 0.75 V p-p |
| RF Input Power | 0 dBm |
| External LO Power | 10 dBm |
| Thermal Resistance (R _{TH}), Junction to Ground Paddle | 8.23°C/W |
| Storage Temperature | -55°C to +150°C |
| Operating Temperature | -40°C to 85°C |
| Reflow Temperature (Maximum Peak) | 260°C |
| ESD Sensitivity, Charged Device Model (CDM) | Class C3 (250 V) |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

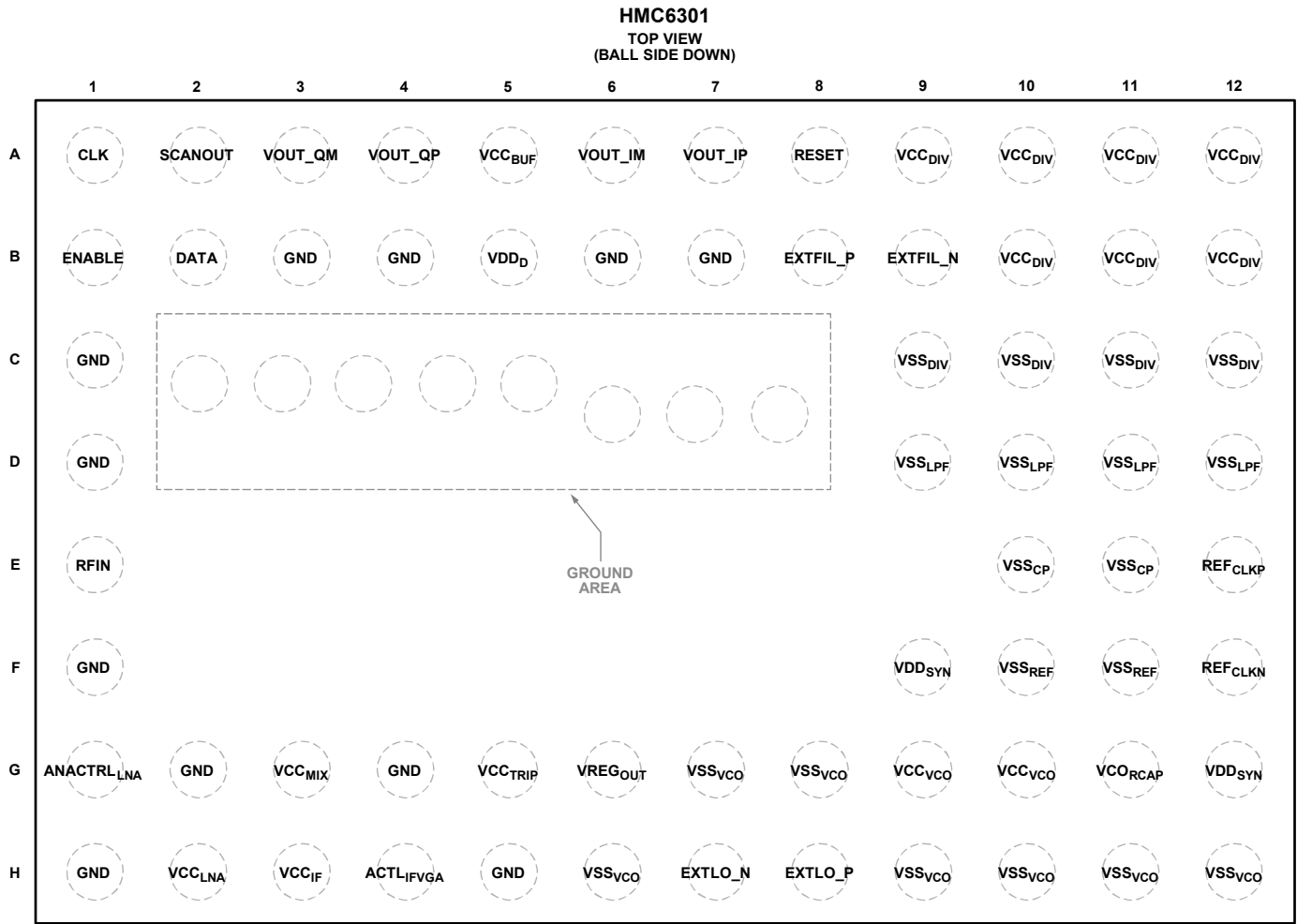


Figure 2. Pin Configuration Diagram

Table 5. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
|--|--------------------|---|
| A1 | CLK | Serial Digital Interface Clock (1.2 V CMOS). |
| A2 | SCANOUT | Serial Digital Interface Out (1.2 V CMOS). |
| A3 | VOUT_QM | Quadrature Negative Baseband Input. This pin is dc-coupled and matched to 50 Ω. |
| A4 | VOUT_QP | Quadrature Positive Baseband Input. This pin is dc-coupled and matched to 50 Ω. |
| A5 | VCC _{BUF} | Power Supply for the Buffer (2.7 V dc). |
| A6 | VOUT_IM | In-Phase Negative Baseband Input. This pin is dc-coupled and matched to 50 Ω. |
| A7 | VOUT_IP | In-Phase Positive Baseband Input. This pin is dc-coupled and matched to 50 Ω. |
| A8 | RESET | Serial Digital Interface Reset (1.2 V CMOS). |
| A9 to A12, B10 to B12 | VCC _{DIV} | Power Supply for the Divider (2.7 V dc). |
| B1 | ENABLE | Serial Digital Interface Enable (1.2 V CMOS). |
| B2 | DATA | Serial Digital Interface Data (1.2 V CMOS). |
| B3, B4, B6, B7, C1, D1, F1, G2, G4, H1, H5 | GND | Analog Ground Connect. |
| B5 | VDD _D | Power Supply for the Digital Circuits (1.3 V dc). |
| B8 | EXTFIL_P | External PLL Loop Filter (Positive). |
| B9 | EXTFIL_N | External PLL Loop Filter (Negative). |

| Pin No. | Mnemonic | Description |
|-----------------------|------------------------|--|
| C9 to C12 | VSS _{DIV} | Digital Ground for the Synthesizer Divider. |
| D9 to D12 | VSS _{LFP} | Digital Ground for the Synthesizer Low-Pass Filter. |
| E1 | RFIN | Radio Frequency Input. This pin is ac-coupled and matched to 50 Ω. |
| E10, E11 | VSS _{CP} | Digital Ground for the Synthesizer Charge Pump. |
| E12 | REF _{CLKP} | External Reference Clock (Positive). This pin can be dc or ac matched to 50 Ω. |
| F9, G12 | VDD _{SYN} | Power Supply for the Synthesizer (1.3 V dc). |
| F10, F11 | VSS _{REF} | Digital Ground for the Synthesizer Reference. |
| F12 | REF _{CLKN} | External Reference Clock (Negative). This pin can be dc or ac matched to 50 Ω. |
| G1 | ANACTRL _{LNA} | Analog Gain Control for the Low Noise Amplifier. Leave this pin floating for digital control. |
| G3 | VCC _{MIX} | Power Supply for the Mixer (2.7 V dc). |
| G5 | VCC _{TRIP} | Power Supply for the Tripler (2.7 V dc). |
| G6 | VREG _{OUT} | Regulator Output for the Voltage Controlled Oscillator. |
| G7, G8, H6, H9 to H12 | VSS _{VCO} | Digital Ground to the Synthesizer Voltage Controlled Oscillator. |
| G9, G10 | VCC _{VCO} | Power Supply for the Voltage Controlled Oscillator (2.7 V dc). |
| G11 | VCC _{RCAP} | External Capacitor Connection for the Voltage Controlled Oscillator Regulator. |
| H2 | VCO _{LNA} | Power Supply for the Low Noise Amplifier (2.8 V dc). |
| H3 | VCC _{IF} | Power Supply for the Intermediate Frequency (2.8 V dc). |
| H4 | ACTL _{IFVGA} | Analog Gain Control for the IF Variable Gain Amplifier. Leave this pin floating for digital control. |
| H7 | EXTLO _{_N} | External Local Oscillator (Negative) Input. |
| H8 | EXTLO _{_P} | External Local Oscillator (Positive) Input. |

TYPICAL PERFORMANCE CHARACTERISTICS

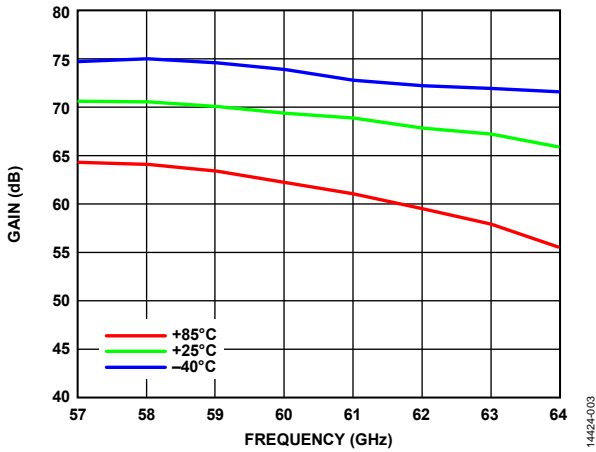


Figure 3. Maximum Gain vs. Frequency over Temperature, IF and RF Attenuation = 0 dBm

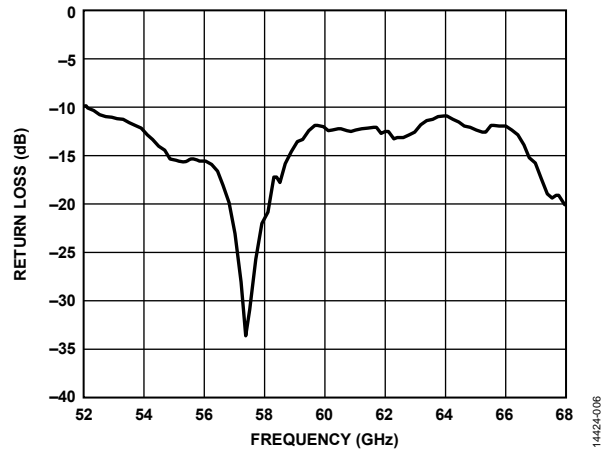


Figure 6. Return Loss vs. Frequency

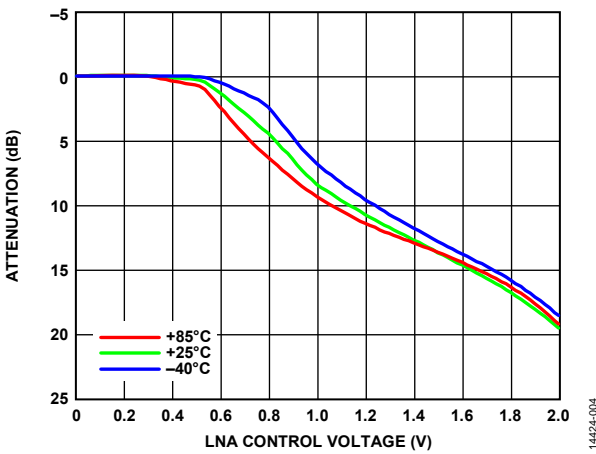


Figure 4. LNA Attenuation vs. Analog Control Voltage over Temperature, Measurement Taken at 60 GHz, IF Attenuation = 0 dBm

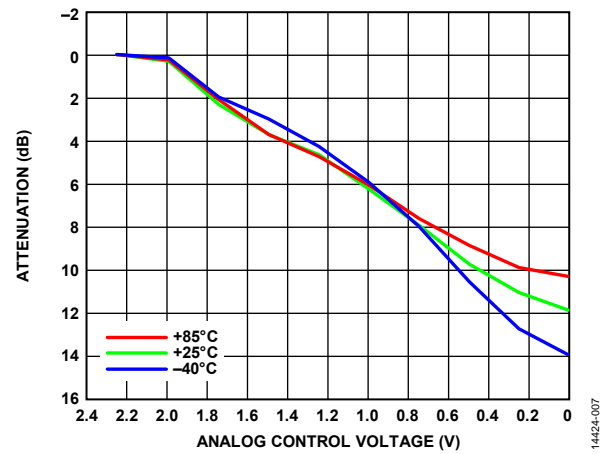


Figure 7. IF Attenuation vs. Analog Control Voltage over Temperature, Measurement Taken at 60 GHz, RF Attenuation = 0 dBm

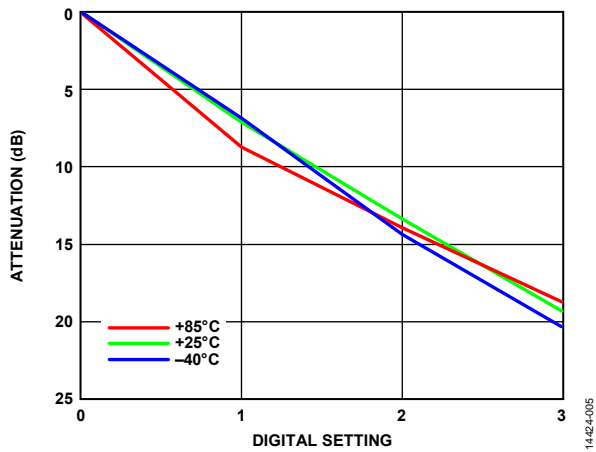


Figure 5. LNA Attenuation vs. Digital Setting over Temperature, Measurement Taken at 60 GHz, IF Attenuation = 0 dBm

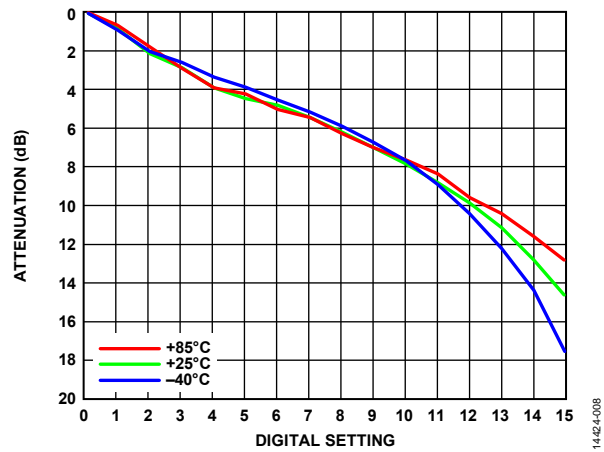


Figure 8. IF Attenuation vs. Digital Setting over Temperature, Measurement Taken at 60 GHz, RF Attenuation = 0 dBm

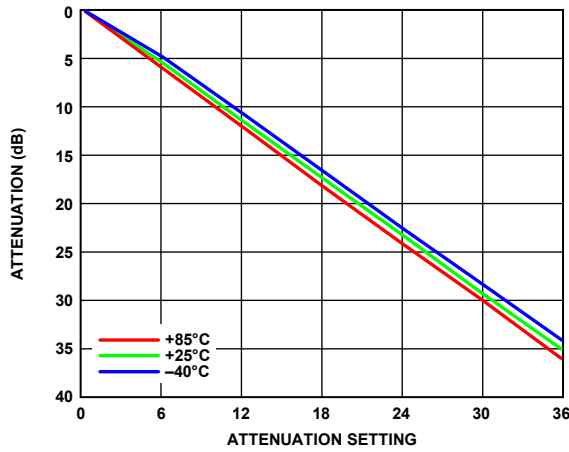


Figure 9. Baseband Attenuation vs. Attenuation Setting over Temperature, Measurement Taken at 60 GHz

14424-009

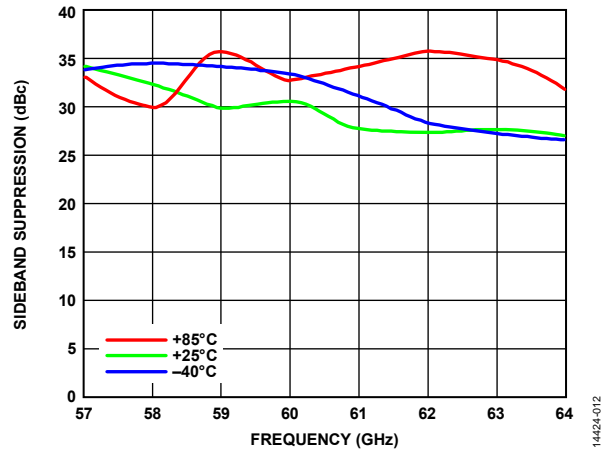


Figure 12. Sideband Suppression vs. Frequency over Temperature, Measurement Taken at Maximum Gain

14424-012

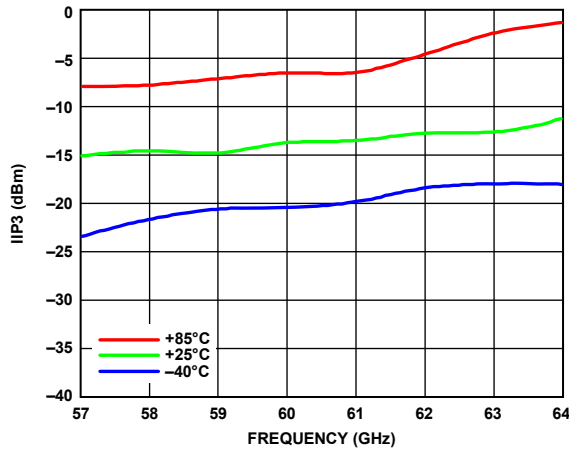


Figure 10. Input IP3 (IIP3) vs. Frequency over Temperature, Minimum LNA Gain, Measurement Taken at Maximum IF Gain and Maximum Baseband Attenuation

14424-010

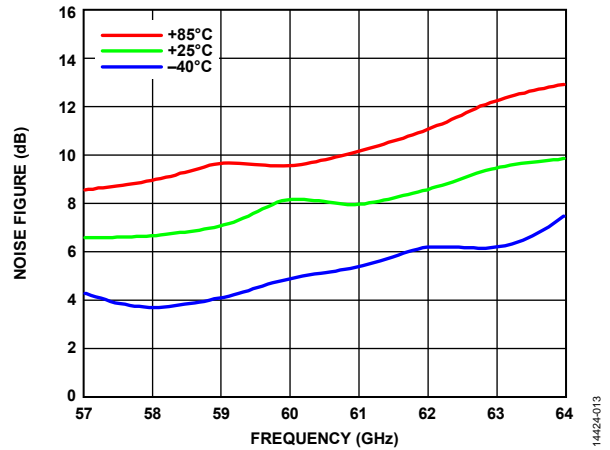


Figure 13. Noise Figure vs. Frequency over Temperature

14424-013

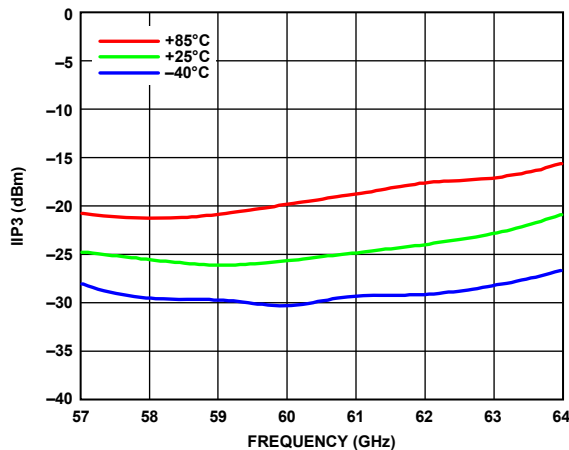


Figure 11. Input IP3 (IIP3) vs. Frequency over Temperature, Minimum LNA Gain, Measurement Taken at Maximum IF Gain and Maximum Baseband Attenuation

14424-011

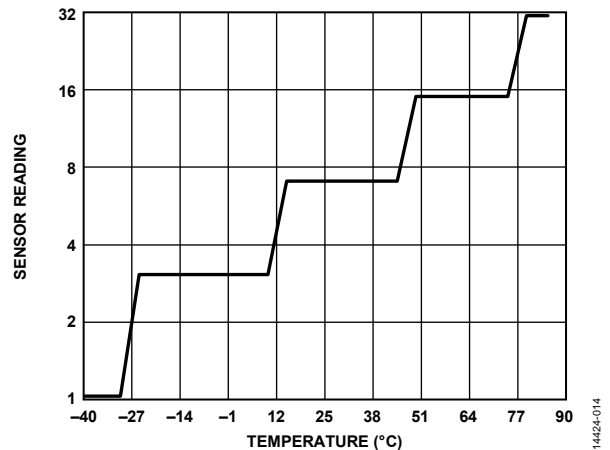


Figure 14. Temperature Sensor Reading vs. Temperature

14424-014

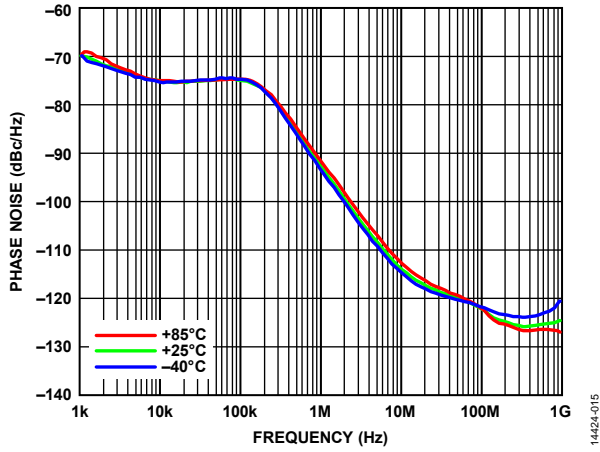


Figure 15. Phase Noise vs. Frequency Offset over Temperature, Internal LO, Measurement Taken at 60 GHz and Nominal Bias

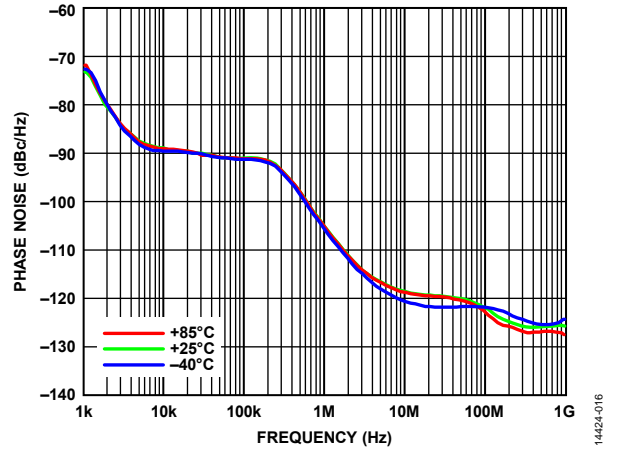


Figure 16. Phase Noise vs. Frequency Offset over Temperature, External LO, Measurement Taken at 60 GHz and Nominal Bias

THEORY OF OPERATION

An integrated frequency synthesizer creates a low phase noise LO between 16.3 GHz and 18.3 GHz. The step size of the synthesizer equates to 250 MHz steps at RF when used with a 71.42857 MHz reference crystal or to 500 MHz if used with a 142.857 reference crystal. To support IEEE channels (ISM band) with a 540 MHz step size, use a 154.2857 MHz reference crystal.

A 57 GHz to 64 GHz signal enters the chip through a single-ended LNA input. The LNA provides 20 dB of variable gain. The LO is multiplied by three and mixed with the LNA output to downconvert to an 8.14 GHz to 9.1 GHz sliding IF. An integrated notch filter removes the image frequency at 40 GHz to 46 GHz. The IF signal is filtered and amplified with 14 dB of variable gain. If the chip is configured for I/Q baseband output, the IF signal feeds into a quadrature demodulator using the LO/2 to downconvert to baseband. There are also options to use on-chip demodulators capable of demodulating AM/FM/FSK/MSK waveforms.

The phase noise and quadrature balance of the on-chip synthesizer is sufficient to support up to 64 QAM modulation. For higher order modulation up to 256 QAM or less than a 250 MHz step size, the HMC6301 can operate using an external LO.

The HMC6301 receiver is ideal for FDD operation along with the HMC6300 transmitter chip. However, both devices can support TDD operation by enabling and disabling the circuits. All of the enables are placed in Register Array 4, allowing full chip enable or disable in one SPI write.

There are no special power sequencing requirements for the HMC6301; apply all voltages simultaneously.

REGISTER ARRAY ASSIGNMENT AND SERIAL INTERFACE

The register arrays for both the receiver and transmitter are organized into 32 rows of 8 bits. Using the serial interface, the arrays are written to or read from one row at a time, as shown in Figure 17 and Figure 18, respectively. Figure 17 shows the sequence of signals on the ENABLE, CLK, and DATA lines to write one 8-bit row of the register array. The ENABLE line goes low, the first of 18 data bits (Bit 0) is placed on the DATA line, and 2 ns or more after the DATA line stabilizes, the CLK line goes high to clock in Data Bit 0. The DATA line must remain stable for at least 2 ns after the rising edge of CLK.

A write operation requires 18 data bits and 18 clock pulses, as shown in Figure 17. The 18 data bits contain the 8-bit register array row data (the least significant bit (LSB) is clocked in first), followed by the register array row address (ROW0 through ROW23, 000000 to 001111, LSB first), the read/write bit (set to 1 to write), and finally, the receiver chip address, 111, LSB first).

The receiver IC serial interface was tested to 500 MHz, and the interface is 1.2 V CMOS levels.

Note that the register array row address is 6 bits but only four are used to designate 32 rows, the two most significant bits (MSBs) are 0.

After the 18th clock pulse of the write operation, the ENABLE line returns high to load the register array on the IC; prior to the rising edge of the ENABLE line, no data is written to the array. The CLK line should have stabilized in the low state at least 2 ns prior to the rising edge of the ENABLE line.

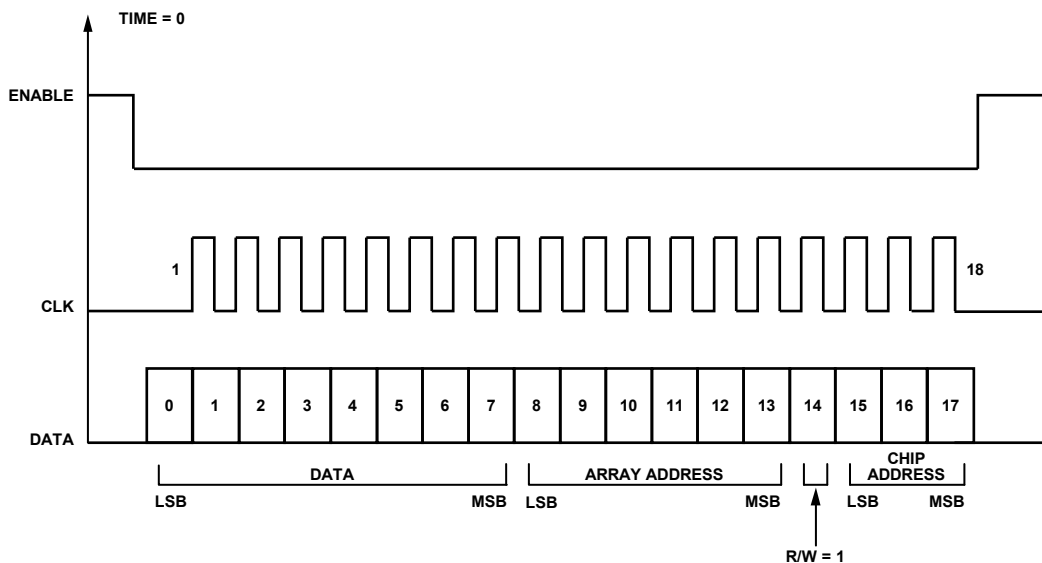


Figure 17. Timing Diagram for Writing a Row of the Receiver Serial Interface

14424-017

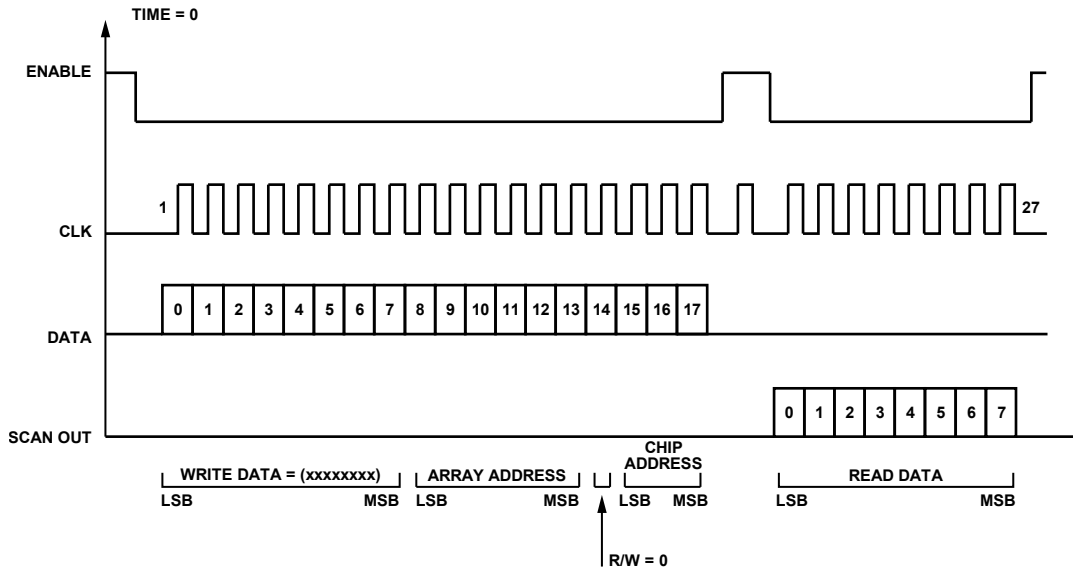


Figure 18. Timing Diagram for Reading a Row of the Receiver Serial Interface

14424-018

RECEIVER REGISTER ARRAY ASSIGNMENTS

All register arrays are read/write, unless otherwise noted.

Table 6. Receiver Register Array Assignments

| Register Array Row, Bit | Internal Signal Name | Signal Function | |
|-------------------------|-----------------------------------|--|--|
| ROW0 | | | |
| ROW0, Bit 7 | lna_pwrdown | Active high to power down the LNA. | |
| ROW0, Bit 6 | bbamp_pwrdown_i | Active high to power down the baseband I channel. | |
| ROW0, Bit 5 | bbamp_pwrdown_q | Active high to power down the baseband Q channel. | |
| ROW0, Bit 4 | divider_pwrdown | Active high to power down the LO divider. | |
| ROW0, Bit 3 | mixer_pwrdown | Active high to power down the RF mixer. | |
| ROW0, Bit 2 | ifmixer_pwrdown/ifmixer_pwrdown_i | Active high to power down the I channel IF mixer. | |
| ROW0, Bit 1 | tripler_pwrdown | Active high to power down the LO tripler. | |
| ROW0, Bit 0 | ifvga_pwrdown | Active high to power down the IF VGA. | |
| ROW1 | | | |
| ROW1, Bit 7 | ipc_pwrdown | Active high to power down on-chip current reference generator. | |
| ROW1, Bit 6 | ifmix_pwrdown_q | Active high to power down the Q channel IF mixer. | |
| ROW1, Bit 5 | if_bgmux_pwrdown | Active high to power down one of the three on-chip band gap references (IF) and associated mux. | |
| ROW1, Bit 4 | ask_pwrdown | Active high to power down the ASK demodulator. | |
| ROW1, Bit 3 | bbamp_atten1_0 | Controls first baseband attenuator; ROW1, Bits[2:3]. 11 is 18 dB attenuation. 10 is 12 dB attenuation. 01 is 6 dB attenuation. 00 is 0 dB attenuation. | |
| ROW1, Bit 2 | bbamp_atten1_1 | | |
| ROW1, Bit 1 | bbamp_sell_ask | | Active high to multiplex the AM detector output into the I channel baseband amplifier input. |
| ROW1, Bit 0 | bbamp_sigshort | | Active high to short the input to the I and Q channel baseband amplifiers. |

| Register Array Row, Bit | Internal Signal Name | Signal Function |
|-------------------------|----------------------|---|
| ROW2 | | |
| ROW2, Bit 7 | bbamp_attenfi_0 | Controls I channel baseband fine attenuator; ROW2[5:7]. 101 is 5 dB attenuation. 100 is 4 dB attenuation. 011 is 3 dB attenuation. 010 is 2 dB attenuation. 001 is 1 dB attenuation. 000 is 0 dB attenuation. |
| ROW2, Bit 6 | bbamp_attenfi_1 | |
| ROW2, Bit 5 | bbamp_attenfi_2 | |
| ROW2, Bit 4 | bbamp_attenfq_0 | Controls Q channel baseband fine attenuator; ROW2[2:4]. 101 is 5 dB attenuation. 100 is 4 dB attenuation. 011 is 3 dB attenuation. 010 is 2 dB attenuation. 001 is 1 dB attenuation. 000 is 0 dB attenuation. |
| ROW2, Bit 3 | bbamp_attenfq_1 | |
| ROW2, Bit 2 | bbamp_attenfq_2 | |
| ROW2, Bit 1 | bbamp_atten2_0 | Controls second bandband attenuator; ROW2[0:1]. 11 is 18 dB attenuation. 10 is 12 dB attenuation. 01 is 6 dB attenuation. 00 is 0 dB attenuation. |
| ROW2, Bit 0 | bbamp_atten2_1 | |
| ROW3 | | |
| ROW3, Bit 7 | bbamp_selbw0 | Selects the low-pass corner of the baseband amplifiers; ROW3[6:7]. 00 is \approx 1.4 GHz. 01 is \approx 500 MHz. 10 is \approx 300 MHz. 11 is \approx 200 MHz. |
| ROW3, Bit 6 | bbamp_selbw1 | |
| ROW3, Bit 5 | bbamp_selfastrec | Selects the high-pass corner of the baseband amplifiers; ROW3[4:5]. 00 is \approx 45 kHz. 01 is \approx 350 kHz. 10 is \approx 1.6 MHz. |
| ROW3, Bit 4 | bbamp_selfastrec2 | |
| ROW3, Bit 3 | bg_monitor_sel<1> | For diagnostic purposes; ROW3[3:0] = 0011 for normal operation. |
| ROW3, Bit 2 | bg_monitor_sel<0> | |
| ROW3, Bit 1 | if_refsel | |
| ROW3, Bit 0 | ina_refsel | |
| ROW4 | | |
| ROW4, Bit 7 | ifvga_bias<2> | Controls bias and IF filter alignment in the IF variable gain amplifier; ROW4[7:1] = 1001111 for normal operation |
| ROW4, Bit 6 | ifvga_bias<1> | |
| ROW4, Bit 5 | ifvga_bias<0> | |
| ROW4, Bit 4 | ifvga_tune<3> | |
| ROW4, Bit 3 | ifvga_tune<2> | |
| ROW4, Bit 2 | ifvga_tune<1> | |
| ROW4, Bit 1 | ifvga_tune<0> | |
| ROW4, Bit 0 | enDigVGA | Active high to enable the digital control of the IF VGA gain |
| ROW5 | | |
| ROW5, Bit 7 | ifvga_vga_adj<3> | Controls IF variable gain amplifier; ROW5[7:4]. 0000 is the highest gain. 1111 is the lowest gain. |
| ROW5, Bit 6 | ifvga_vga_adj<2> | |
| ROW5, Bit 5 | ifvga_vga_adj<1> | Controls IF filter alignment in the RF mixer; ROW5[3:0] = 1111 for normal operation. |
| ROW5, Bit 4 | ifvga_vga_adj<0> | |
| ROW5, Bit 3 | rfmix_tune<3> | |
| ROW5, Bit 2 | rfmix_tune<2> | |
| ROW5, Bit 1 | rfmix_tune<1> | |
| ROW5, Bit 0 | rfmix_tune<0> | |

| Register Array Row, Bit | Internal Signal Name | Signal Function |
|--|--|--|
| ROW6 ROW6, Bit 7 ROW6, Bit 6 ROW6, Bit 5 ROW6, Bit 4 ROW6, Bit 3 ROW6, Bit 2 ROW6, Bit 1 ROW6, Bit 0 | tripler_bias<13> tripler_bias<12> tripler_bias<11> tripler_bias<10> tripler_bias<9> tripler_bias<8> tripler_bias<7> tripler_bias<6> | Controls the bias of the frequency tripler; ROW6[7:0] = 10111111 for normal operation. |
| ROW7 ROW7, Bit 7 ROW7, Bit 6 ROW7, Bit 5 ROW7, Bit 4 ROW7, Bit 3 ROW7, Bit 2 ROW7, Bit 1 ROW7, Bit 0 | tripler_bias<5> tripler_bias<4> tripler_bias<3> tripler_bias<2> tripler_bias<1> tripler_bias<0> bbamp_selfm fm_pwrdn | Controls the bias of the frequency tripler; ROW7[7:2] = 011011 for normal operation. Active high to multiplex the FM detector output into the Q channel baseband amplifier input. Active high to power down FM demodulator. |
| ROW8 ROW8, Bit 7 ROW8, Bit 6 ROW8, Bit 5 ROW8, Bit 4 ROW8, Bit 3 ROW8, Bit 2 ROW8, Bit 1 ROW8, Bit 0 | lna_bias<2> lna_bias<1> lna_bias<0> lna_gain<1> na_gain<0> ifvga_q_cntrl<2> ifvga_q_cntrl<1> ifvga_q_cntrl<0> | Controls bias of the low noise amplifier; ROW8[7:5] = 100 for normal operation. Controls LNA variable gain; ROW8[4:3]. 00 is the highest gain. 11 is the lowest gain. Controls the Q of the IF filter in the IF variable gain amplifier; ROW8[2:0] = 000 for the highest Q and the highest gain. To reduce Q and widen bandwidth, increment ROW8[2:0] in the sequence: 001 100 101 111. |
| ROW9 ROW9, Bit 7 ROW9, Bit 6 ROW9, Bit 5 ROW9, Bit 4 ROW9, Bit 3 ROW9, Bit 2 ROW9, Bit 1 ROW9, Bit 0 | enAnaV_LNA enbar_TempS en_tempFlash en_Sep_ifmix_pwrdn_q Not used Not used Not used Not used | Active high enable analog gain control of the LNA. Active high to power down the temperature sensor. Active high to enable the temperature sensor. Enable separate power down for the IF mixer I/Q 0 for normal operation. Not used. Not used. Not used. Not used. |
| ROW10 | Not used | Not used. |
| ROW11 | Not used | Not used. |
| ROW12 | Not used | Not used. |
| ROW13 | Not used | Not used. |
| ROW14 | Not used | Not used. |
| ROW15 | Not used | Not used. |

| Register Array Row, Bit | Internal Signal Name | Signal Function |
|-------------------------|----------------------|---|
| ROW16 | | |
| ROW16, Bit 7 | byp_synth_LDO | Factory diagnostics, 0 for normal operation. |
| ROW16, Bit 6 | en_cpShort | Factory diagnostics, 0 for normal operation. |
| ROW16, Bit 5 | en_cpCMFB | Enables CMFB circuit for charge pump, set to 1 when synthesizer is in use. |
| ROW16, Bit 4 | en_cp_dump | Enables auxiliary circuit for charge pump, set to 1 when synthesizer is in use. |
| ROW16, Bit 3 | en_cpTRIST | Factory diagnostics, 0 for normal operation. |
| ROW16, Bit 2 | en_cp | Enables charge pump, set to 1 when synthesizer is in use. |
| ROW16, Bit 1 | en_synth_LDO | Enables LDO for synthesizer, set to 1 when synthesizer is in use. |
| ROW16, Bit 0 | enbar_synthBG | Factory diagnostics, 0 for normal operation. |
| ROW17 | | |
| ROW17, Bit 7 | en_lockd_clk | Enables lock detector for synthesizer, set to 1 when synthesizer is in use. |
| ROW17, Bit 6 | en_test_divOut | Factory diagnostics, 0 for normal operation. |
| ROW17, Bit 5 | en_vtune_flash | Enables flash ADCs for VCO vtune port, set to 1 when synthesizer is in use. |
| ROW17, Bit 4 | en_reBuf_DC | Enables dc coupling for reference clock buffer. |
| ROW17, Bit 3 | en_refBuf | Enables reference clock buffer, set to 1 when synthesizer is in use. |
| ROW17, Bit 2 | en_stick_div | Factory diagnostics, 0 for normal operation. |
| ROW17, Bit 1 | en_FBDiv_cml2cmos | Enables auxiliary circuit for the feedback divider chain, set to 1 when synthesizer is in use. |
| ROW17, Bit 0 | en_FBDiv | Enables feedback divider chain, set to 1 when synthesizer is in use. |
| ROW18 | | |
| ROW18, Bit 7 | Not used. | Not used. |
| ROW18, Bit 6 | en_nb250m | Active high to enable 250 MHz channel step size. |
| ROW18, Bit 5 | byp_vco_LDO | Factory diagnostics, 0 for normal operation. |
| ROW18, Bit 4 | en_extLO | Enables external LO, set to 0 when synthesizer is in use. |
| ROW18, Bit 3 | en_vcoPk | Factory diagnostics, 0 for normal operation. |
| ROW18, Bit 2 | en_vco | Enables internal VCO, set to 1 when synthesizer is in use. |
| ROW18, Bit 1 | en_vco_reg | Enables internal regulator for VCO, set to 1 when synthesizer is in use. |
| ROW18, Bit 0 | enbar_vcoGB | Factory diagnostics, 0 for normal operation. |
| ROW19 | | |
| ROW19, Bit 7 | Not used | Not used. |
| ROW19, Bit 6 | Not used | Not used. |
| ROW19, Bit 5 | Not used | Not used. |
| ROW19, Bit 4 | Not used | Not used. |
| ROW19, Bit 3 | Not used | Not used. |
| ROW19, Bit 2 | Not used | Not used. |
| ROW19, Bit 1 | refsel_synthBG | Factory diagnostics, 1 for normal operation. |
| ROW19, Bit 0 | muxRef | Factory diagnostics, 0 for normal operation. |
| ROW20 | | |
| ROW20, Bit 7 | Not used | Not used. |
| ROW20, Bit 6 | Fbdiv_code<6> | Feedback divider ratio for the integer-N internal synthesizer based on Table 7, Table 8, and Table 9. |
| ROW20, Bit 5 | Fbdiv_code<5> | |
| ROW20, Bit 4 | Fbdiv_code<4> | |
| ROW20, Bit 3 | Fbdiv_code<3> | |
| ROW20, Bit 2 | Fbdiv_code<2> | |
| ROW20, Bit 1 | Fbdiv_code<1> | |
| ROW20, Bit 0 | Fbdiv_code<0> | |

| Register Array Row, Bit | Internal Signal Name | Signal Function |
|---|--|--|
| ROW21 ROW21, Bit 7 ROW21, Bit 6 ROW21, Bit 5 ROW21, Bit 4 ROW21, Bit 3 ROW21, Bit 2 ROW21, Bit 1 ROW21, Bit 0 | Not used Not used Not used refsel_vcoBG vco_biasTrim<3> vco_biasTrim<2> vco_biasTrim<1> vco_biasTrim<0> | Not used. Not used. Not used. Factory diagnostics, 1 for normal operation. Sets VCO tank bias current ROW21[3:0] = 0010 for normal operation. |
| ROW22 ROW22, Bit 7 ROW22, Bit 6 ROW22, Bit 5 ROW22, Bit 4 ROW22, Bit 3 ROW22, Bit 2 ROW22, Bit 1 ROW22, Bit 0 | Not used Not used Not used vco_bandSel<4> vco_bandSel<3> vco_bandSel<2> vco_bandSel<1> vco_bandSel<0> | Not used. Not used. Not used. Set for desired frequency. Table 7, Table 8, and Table 9. contain approximate band setting depending on reference clock frequency. ROW22[4:0] = valid range 00000-10011. |
| ROW23 ROW23, Bit 7 ROW23, Bit 6 ROW23, Bit 5 ROW23, Bit 4 ROW23, Bit 3 ROW23, Bit 2 ROW23, Bit 1 ROW23, Bit 0 | ICP_BiasTrim<2> ICP_BiasTrim<1> ICP_BiasTrim<0> vco_offset<0> vco_offset<1> vco_offset<2> vco_offset<3> vco_offset<4> | Sets charge pump current. ROW23[7:5] = 011 for normal operation. Sets internal VCO output swing. ROW23[4:0] = 00010 for normal operation. |
| ROW24 (Read Only) ROW24, Bit 7 ROW24, Bit 6 ROW24, Bit 5 ROW24, Bit 4 ROW24, Bit 3 ROW24, Bit 2 ROW24, Bit 1 ROW24, Bit 0 | Not used Not used Not used Not used lockdet dn up center | Not used. Not used. Not used. Not used. Monitor for lock detect, 1 indicates valid lock. Monitor VCO amplitude. Monitor VCO amplitude. Monitor VCO amplitude. |
| ROW25 (Read Only) ROW25, Bit 7 ROW25, Bit 6 ROW25, Bit 5 ROW25, Bit 4 ROW25, Bit 3 ROW25, Bit 2 ROW25, Bit 1 ROW25, Bit 0 | vtune_flashp<7> vtune_flashp<6> vtune_flashp<5> vtune_flashp<4> vtune_flashp<3> vtune_flashp<2> vtune_flashp<1> vtune_flashp<0> | VCO amplitude monitor (positive). |

| Register Array Row, Bit | Internal Signal Name | Signal Function |
|-------------------------|----------------------|--|
| ROW26 (Read Only) | | |
| ROW26, Bit 7 | vtune_flashn<7> | VCO amplitude monitor (negative). |
| ROW26, Bit 6 | vtune_flashn<6> | |
| ROW26, Bit 5 | vtune_flashn<5> | |
| ROW26, Bit 4 | vtune_flashn<4> | |
| ROW26, Bit 3 | vtune_flashn<3> | |
| ROW26, Bit 2 | vtune_flashn<2> | |
| ROW26, Bit 1 | vtune_flashn<1> | |
| ROW26, Bit 0 | vtune_flashn<0> | |
| ROW27 (Read Only) | | |
| ROW27, Bit 7 | Not used | Not used. |
| ROW27, Bit 6 | Not used | Not used. |
| ROW27, Bit 5 | Not used | Not used. |
| ROW27, Bit 4 | tempS<4> | Thermometer encoded temperature reading. ROW27[4:0] = the following: 00000 is the lowest temperature. 11111 is the highest temperature. |
| ROW27, Bit 3 | tempS<3> | |
| ROW27, Bit 2 | tempS<2> | |
| ROW27, Bit 1 | tempS<1> | |
| ROW27, Bit 0 | tempS<0> | |
| ROW28 | Not used | Not used. |
| ROW29 | Not used | Not used. |
| ROW30 | Not used | Not used. |
| ROW31 | Not used | Not used. |

Synthesizer Settings**Table 7. Synthesizer Settings, IEEE Channels Using 154.2857 MHz Reference**

| Frequency (GHz) | IEEE Channel | Divider Setting, Fbdiv_Code<5:0>, ROW20, Bits[5:0] | Typical Band Setting, vco_bandSel<4:0>, ROW22, Bits[4:0] |
|-----------------|--------------|--|--|
| 57.24 | | 001010 | 00001 |
| 57.78 | | 001011 | 00010 |
| 58.32 | Channel 1 | 001100 | 00010 |
| 58.86 | | 001101 | 00010 |
| 59.40 | | 001110 | 00011 |
| 59.94 | | 001111 | 00011 |
| 60.48 | Channel 2 | 010000 | 00100 |
| 61.02 | | 010001 | 00100 |
| 61.56 | | 010010 | 00101 |
| 62.10 | | 010011 | 00101 |
| 62.64 | Channel 3 | 010100 | 00101 |
| 63.18 | | 010101 | 00110 |
| 63.72 | | 010110 | 00110 |
| 64.26 | | 010111 | 00110 |
| 64.8 | Channel 4 | 011000 | 00111 |
| 65.34 | | 011001 | 00111 |
| 65.88 | | 011010 | 01000 |

Table 8. 500 MHz Channels Using 142.8571 MHz Reference

| Frequency (GHz) | Divider Setting | Typical Band Setting |
|-----------------|-----------------|----------------------|
| 56.5 | 010001 | 00001 |
| 57 | 010010 | 00001 |
| 57.5 | 010011 | 00010 |
| 58 | 010100 | 00010 |
| 58.5 | 010101 | 00010 |
| 59 | 010110 | 00011 |
| 59.5 | 010111 | 00011 |
| 60 | 011000 | 00100 |
| 60.5 | 011001 | 00100 |
| 61 | 011010 | 00101 |
| 61.5 | 011011 | 00101 |
| 62 | 011100 | 00101 |
| 62.5 | 011101 | 00110 |
| 63 | 011110 | 00110 |
| 63.5 | 011111 | 00110 |
| 64 | 100000 | 00111 |

Table 9. 250 MHz Channels Using 71.42857 MHz Reference

| Frequency (GHz) | Divider Setting | Typical Band Setting |
|------------------------|------------------------|-----------------------------|
| 56.5 | 0100010 | 00001 |
| 56.75 | 0100011 | 00001 |
| 57 | 0100100 | 00010 |
| 57.25 | 0100101 | 00010 |
| 57.5 | 0100110 | 00011 |
| 57.75 | 0100111 | 00011 |
| 58 | 0101000 | 00100 |
| 58.25 | 0101001 | 00100 |
| 58.5 | 0101010 | 00101 |
| 58.75 | 0101011 | 00101 |
| 59 | 0101100 | 00110 |
| 59.25 | 0101101 | 00110 |
| 59.5 | 0101110 | 00111 |
| 59.75 | 0101111 | 00111 |
| 60 | 0110000 | 01000 |
| 60.25 | 0110001 | 01000 |
| 60.5 | 0110010 | 01001 |
| 60.75 | 0110011 | 01001 |
| 61 | 0110100 | 01010 |
| 61.25 | 0110101 | 01010 |
| 61.5 | 0110110 | 01011 |
| 61.75 | 0110111 | 01011 |
| 62 | 0111000 | 01100 |
| 62.25 | 0111001 | 01100 |
| 62.5 | 0111010 | 01101 |
| 62.75 | 0111011 | 01101 |
| 63 | 0111100 | 01110 |
| 63.25 | 0111101 | 01110 |
| 63.5 | 0111110 | 01111 |
| 63.75 | 0111111 | 01111 |
| 64 | 1000000 | 01111 |

APPLICATIONS INFORMATION

For more information about the [HMC6301](#) evaluation kit, see the [EK1HMC6350 User Guide](#). The [EK1HMC6350](#) contains all that is required to set up a simplex 60 GHz millimeterwave link using standard RF cable interfaces for baseband input and output. The kit comes with two motherboard printed circuit

boards (PCBs) that provide on-board crystals, USB interface, supply regulators, and SMA cables for connectorized I/Q interfaces. Software is supplied to allow the user to read from and write to all chip level registers using graphical user interface (GUI) or to upload previously saved register settings.

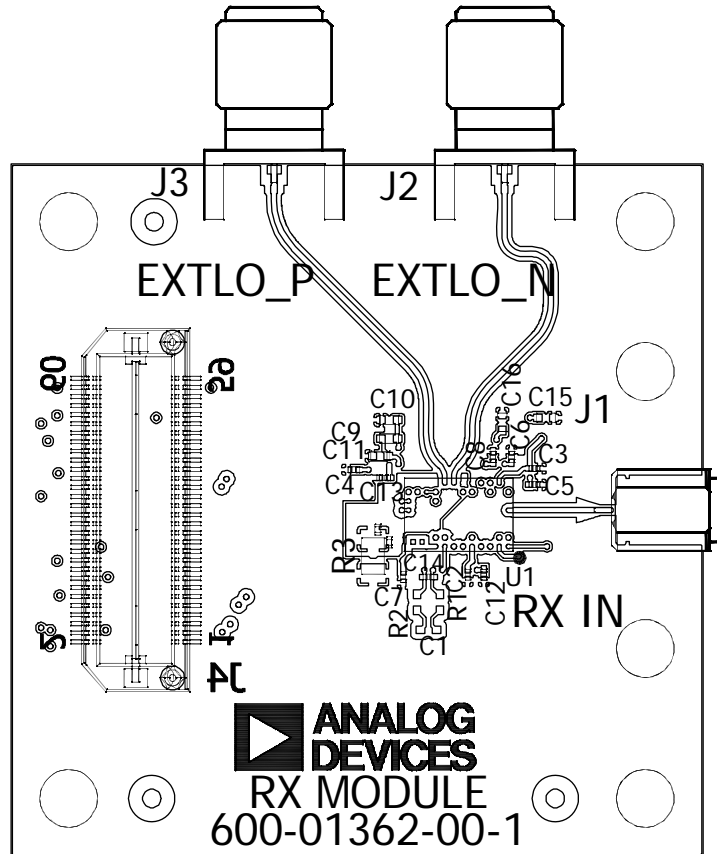
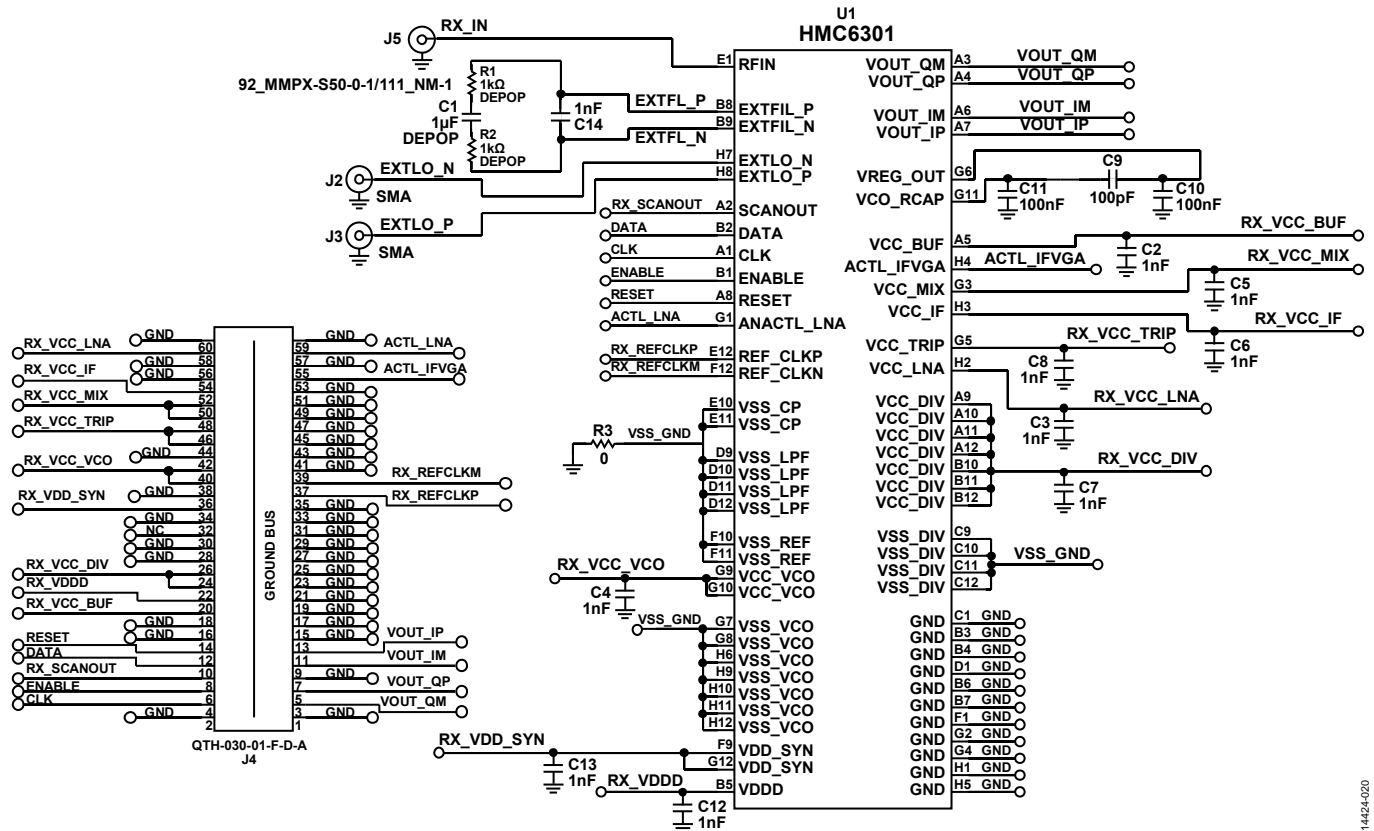


Figure 19. [HMC6301](#) (600-01362-00-1) Evaluation PCB Daughter Board



14424-020

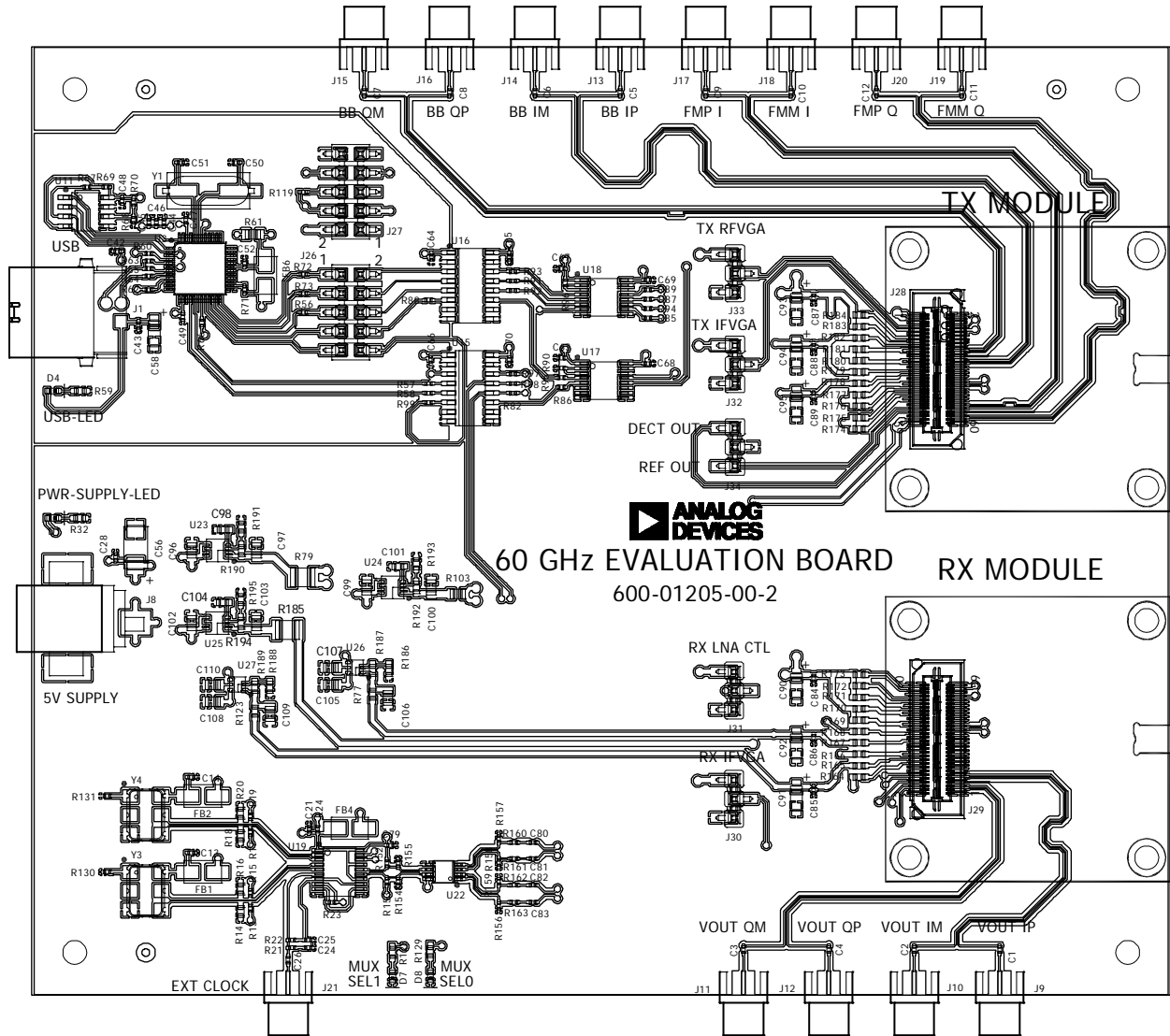


Figure 21. HMC6301 Evaluation PCB Motherboard

14424-021

OUTLINE DIMENSIONS

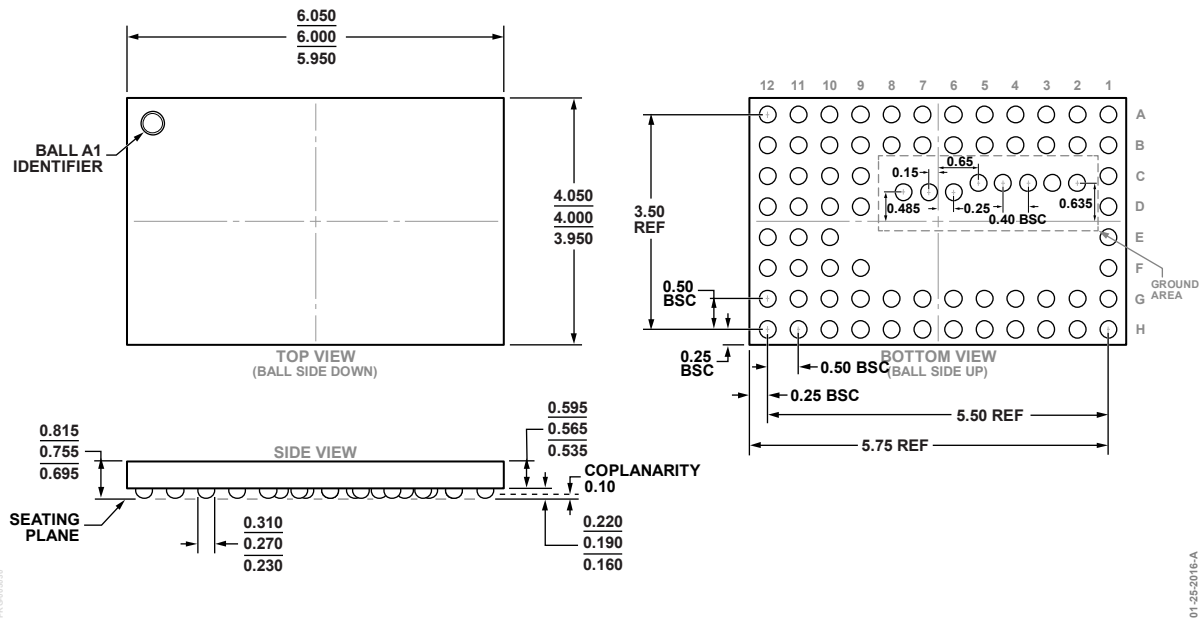


Figure 22. 75-Ball Wafer Level Ball Grid Array [WLBGA] (BF-75-1)
Dimensions shown in millimeters

ORDERING GUIDE

| Model | Temperature Range | Chip Bump Composition | MSL Rating ¹ | Package Description | Package Option | Package Marking ² |
|------------------------------|-------------------|---|-------------------------|---|----------------|-------------------------------|
| HMC6301BG46 | -40°C to +85°C | 96.5 Tin (Sn), 3.0 Silver (Ag), 0.5 Copper (Cu) | MSL1 | 75-Ball WLBGA | BF-75-1 | BBFZ #YYWW XXX XXXXX-XX |
| EV1HMC6301BG46 EK1HMC6350 | | | | Evaluation Board, PCB Only Evaluation Kit Assembly | | |

¹ Maximum peak reflow temperature of 260°C. The peak reflow temperature must not exceed the maximum temperature for which the package is qualified according to the moisture sensitivity level (MSL1).

² BBFZ indicates a Pb-free part, #YYWW indicates the year and week number, and the assembly lot number is indicated by XXX XXXXX-XX.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [RF Receiver](#) category:

Click to view products by [Analog Devices](#) manufacturer:

Other Similar products are found below :

[MICRF011YN](#) [HMC8100LP6JETR](#) [TDA5240](#) [TDA5201XT](#) [TDA5225](#) [ATA8205P6C-TKQW](#) [VRC522](#) [MICRF229YQS](#) [SI4825-A10-CS](#)
[SI4730-D60-GMR](#) [MICRF219AA YQS](#) [AW13412DNR](#) [LT5504EMS8#PBF](#) [AD6677BCPZ](#) [AD6641BCPZ-500](#) [AD6643BCPZ-200](#)
[AD6643BCPZ-250](#) [AD6649BCPZ](#) [AD6649BCPZRL7](#) [AD6650ABC](#) [AD6652BBCZ](#) [AD6655ABCPZ-125](#) [AD6655ABCPZ-150](#)
[AD6655ABCPZ-80](#) [AD6657ABBCZ](#) [AD6657BBCZ](#) [AD6673BCPZ-250](#) [AD6674-1000EBZ](#) [AD6674BCPZ-1000](#) [AD6674BCPZ-500](#)
[AD6676BCBZRL](#) [AD6679BBPZ-500](#) [ADRV9008BBCZ-1](#) [AD9864BCPZ](#) [AD9864BCPZRL](#) [ADAR2004ACCZ](#) [AD9874ABST](#)
[HMC8100LP6JE](#) [LTC5556IUH#PBF](#) [BGT24MR2E6327XUMA1](#) [TDA5211](#) [MICRF011YM](#) [MAX7036GTP/V+](#) [MAX2141ETH/V+](#)
[MAX7033EUI+](#) [MAX1473EUI+T](#) [MAX1473EUI+](#) [MAX1470EUI+](#) [MAX7034AUI+](#) [MAX7034AUI/V+](#)